

1. Material Substrate GaAlAs (N Type) Removed
 Epitaxial Layer GaAlAs (P/N Type)

2. Electrode N(Cathode) Side Gold Alloy
 P(Anode) Side Gold Alloy

3. Electro-Optical Characteristics

Parameter	Symbol	Min	Typ	Max	Unit	Condition
Forward Voltage	$V_{F(1)}$		1.1		V	IF=10uA
	$V_{F(2)}$			1.6	V	IF=50mA
Reverse Voltage	V_R	5			V	IR=10uA
Power	P_O	17			mW	IF=50mA
Wavelength	λ_P		850		nm	IF=50mA
	$\Delta\lambda$		45		nm	IF=50mA
Rise Time	T_r		22		ns	
Fall Time	T_f		13		ns	

※ Note : Power is measured by Sorter E/T system with bare chip.

4. Mechanical Data (a) Emission Area ----- 10.8mil x 10.8mil
 (b) Bottom Area ----- 11.8mil x 11.8mil
 (c) Bonding Pad ----- 110um
 (d) Chip Thickness ----- 7mil
 (e) Junction Height ----- 6.5mil

